





Ultra-low power digital PDM XENSIV™ MEMS microphone

Features

- Low current consumption in normal mode (580µA)
- Ultra-low current consumption in low power mode (190µA)
- Signal-to-noise ratio (SNR) of 66.5dB(A)
- · Very high acoustic overload point at 132dBSPL
- Flat frequency response with low frequency roll-off at 20Hz
- · Component level IP57 dust and water resistant
- Package dimensions: 3.5mm x 2.65mm x 0.98mm
- · Enhanced RF shielding
- · Digital PDM output
- Bottom port

Potential applications

- · Smartphones and mobile devices
- Active Noise Cancellation (ANC) headphones and earbuds
- · High quality audio capturing
 - Laptops and tablets
 - Conference systems
 - Cameras, camcorders, and camera accessories
- Devices with Voice User Interface (VUI)
 - Smart speakers
 - Home automation
 - IOT devices
- Industrial or home monitoring with audio pattern detection

Product validation

Technology qualified for industrial applications.

Ready for validation in industrial applications according to the relevant tests of IEC 60747 and 60749 or alternatively JEDEC47/20/22.

Description

Discover the IM66D132HV01 – an ultra-low power digital XENSIV™ MEMS microphone, designed for applications which require long battery life, very high AOP and environmental robustness in a small package.

With a Signal-to-noise ratio (SNR) of 66.5dB(A) and low corner frequency of 20Hz the microphone enables a clear audio experience without compromising on battery life.

Enabled by a revolutionary digital microphone ASIC, the IM66D132HV01 balances performance in a small package at a low current consumption of $580\mu A$.

Туре	Package	Marking	Ordering code
IM66D132HV01	PG-TLGA-5-9	I66D31	SP006037650









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1 Block diagram



1 Block diagram

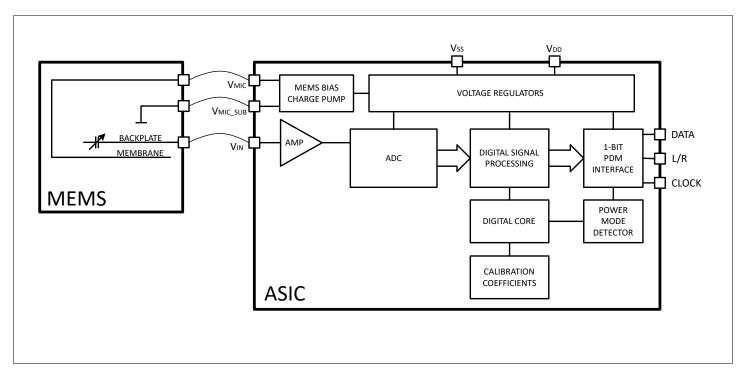


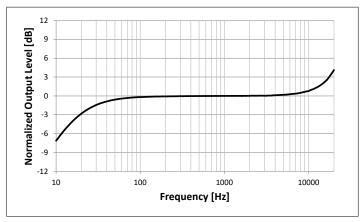
Figure 1 Block diagram





2 Typical performance characteristics

Test conditions: V_{DD} =1.8V, f_{CLK} =3.072MHz, T_A =25°C, unless otherwise specified.



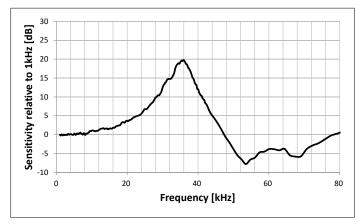


Figure 2 Typical amplitude response

90 75 60 80 45 45 0 -15 -30 10 100 1000 Frequency [Hz]

Figure 3 Typical ultrasonic response

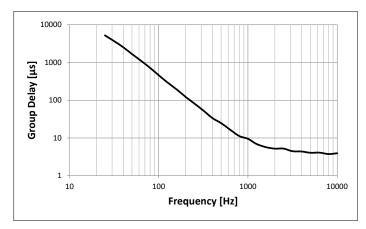


Figure 4 Typical phase response

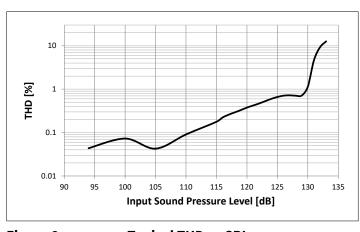


Figure 5 Typical group delay

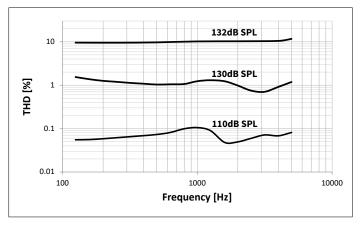


Figure 6 Typical THD vs SPL

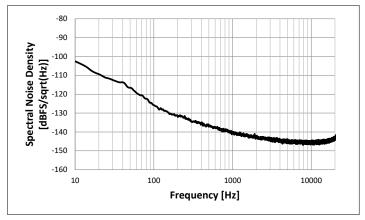
Figure 7 Typical THD vs frequency

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2 Typical performance characteristics



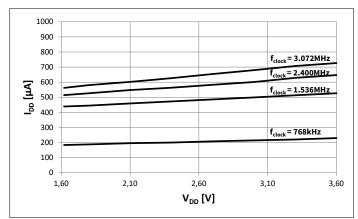


Figure 8 Typical noise floor (unweighted)

Figure 9 Typical I_{DD} vs V_{DD}

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3 Acoustic characteristics



3 Acoustic characteristics

Table 1 Acoustic specifications normal mode

Test conditions (unless otherwise specified in the table): V_{DD} = 1.8V, F_{clock} = 3.072MHz, OSR=64, T_A = 25°C, 55% R.H., audio bandwidth 20 Hz to 20kHz, select pin grounded, no load on DATA, T_{edge} = 9ns

Parameter		Symbol		Values		Unit	Note or Test Condition
			Min.	Тур.	Max.		
Sensitivity		S	-38	-37	-36	dBFS	1kHz, 94dBSPL
Low Frequency I	Roll-off	LFRO		20		Hz	-3dB relative to 1kHz
Resonance Freq	uency Peak			36		kHz	
Signal-to-Noise	F _{clock} = 1.536 MHz	SNR		65.5			20 Hz to 20kHz
Ratio	F _{clock} = 2.0 MHz			66		4D/4/	bandwidth, A-weighted
	F _{clock} = 2.4 MHz			66.2		dB(A)	
	$F_{clock} = 3.072 \text{ MHz}$			66.5			
Total Harmonic	94dBSPL	THD			0.3		Measuring 2nd to 5th harmonics; 1kHz. S=typ
Distortion	130dBSPL			1.0		%	
	132dBSPL			10.0			
Acoustic Overload Point	10% THD	AOP		132		dBSPL	Measuring 2nd to 5th harmonics; 1kHz. S=typ
Group Delay	100Hz			460			
	1kHz			10		μs	
	4kHz			4			
Phase	100Hz			14			
Response	1kHz			0		0	
	4kHz			-5			
Directivity		Omnidirectional					
Polarity			Positive pressure increases density of 1's, negative pressure decreases density of 1's in data output				

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3 Acoustic characteristics



Table 2 Acoustic specifications low power mode

Test conditions (unless otherwise specified in the table): $V_{DD} = 1.8V$, $F_{clock} = 768$ kHz, OSR=48, $T_A = 25$ °C, 55% R.H., audio bandwidth 20 Hz to 8kHz, select pin grounded, no load on DATA, $T_{edge} = 9$ ns

Parameter		Symbol	Symbol Values		Unit	Note or Test Condition	
			Min.	Тур.	Max.		
Sensitivity		S	-22	-21	-20	dBFS	1kHz, 94dBSPL
Signal-to-Noise Ratio	F _{clock} = 768kHz	SNR		63.5		dB(A)	20 Hz to 8kHz bandwidth, A- weighted
Total Harmonic	94dBSPL	THD			0.3		Measuring 2nd to 5th
Distortion	115dBSPL			1.0		%	harmonics; 1kHz. S=typ
	117dBSPL			10.0			
Acoustic Overload Point	10% THD	AOP		117		dBSPL	Measuring 2nd to 5th harmonics; 1kHz. S=typ

4 Free field frequency response



4 Free field frequency response

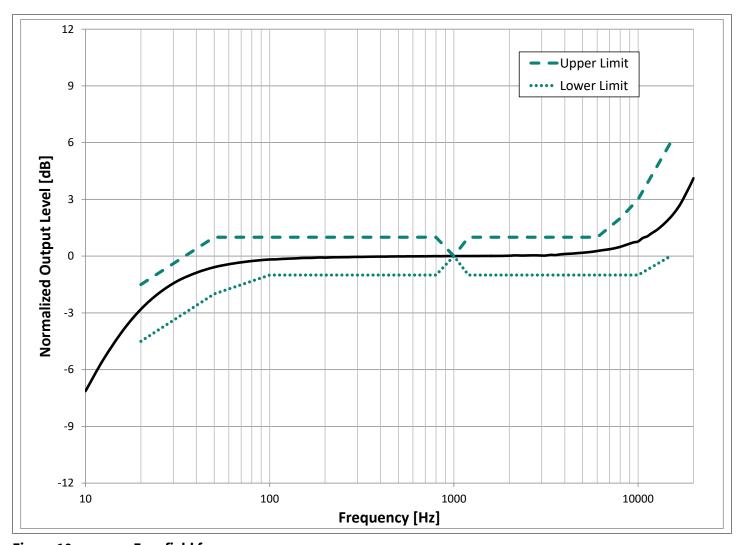


Figure 10 Free field frequency response

Table 3 Free field frequency response, normalized to 1kHz sensitivity value

Frequency [Hz]	Upper limit [dB]	Lower limit [dB]
20	-1.5	-4.5
50	1	-2
100	1	-1
800	1	-1
1000	0	0
1200	1	-1
6000	1	-1
8000	2	-1
10000	3	-1
15000	6	0

5 Electrical characteristics and parameters



5 Electrical characteristics and parameters

5.1 Absolute maximum ratings

Table 4 Absolute maximum ratings

Stresses exceeding the listed maximum ratings may affect device reliability or cause permanent device damage. Functional device operation at these conditions is not guaranteed. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

Parameter	Symbol	Values		Unit	Note/Test Condition
		Min.	Max.		
Voltage on any Pin	V _{Maximum}		3.6	V	
Storage Temperature	T _S	-40	125	°C	1)
Operating Temperature	T _A	-40	85	°C	

5.2 Electrical parameters

Table 5 Electrical parameters and digital interface input

Test conditions (unless otherwise specified in the table): $V_{DD} = 1.8V$, $T_A = 25$ °C, 55% R.H.

Parameter		Symbol		Values			Note/Test Condition
			Min.	Тур.	Max.		
Supply Volta	ge	V_{DD}	1.6	1.8	3.465	V	2)
Clock	Standby Mode	f _{clock}			330	kHz	3)
Frequency Range	Low Power		370	406	440	kHz	4)
Runge	Mode		480	600	650		
			720	768	840		
Normal Mode			930	1000	1220		
	Normal Mode		1.34	1.536	1.72	MHz	
		1.91	2.0	2.09			
			2.31	2.4	2.57		
			2.84	3.072	3.44		
			3.81	4.0	4.18		
V _{DD} Ramp-up	Time				50	ms	Time until V _{DD} ≥ V _{DD_min}
Input Logic L	ow Level	V _{IL}			0.3xV _{DD}	V	
Input Logic F	ligh Level	V _{IH}	0.7xV _{DD}			V	
Clock Rise/Fa	all Time	T _{CR} /T _{CF}			13	ns	10% to 90% of V _{DD}

(table continues...)

Storage of Products Supplied by Infineon Technologies

A $1\mu F$ bypass capacitor shall be placed close to the microphone V_{DD} pad to ensure best SNR performance.

Data pad is high impedance in standby mode.

⁴ The clock frequencies between the switching thresholds of different modes cannot be used.

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5 Electrical characteristics and parameters

Table 5 (continued) Electrical parameters and digital interface input

Test conditions (unless otherwise specified in the table): $V_{DD} = 1.8V$, $T_A = 25$ °C, 55% R.H.

Parameter	Symbol	Values		Unit	Note/Test Condition	
		Min.	Тур.	Max.		
Clock Duty Cycle		45		55	%	
Clock input capacitance	C _{in}		45		pF	
Data output load	C _{load}			100	pF	

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5 Electrical characteristics and parameters



5.3 Electrical characteristics

Table 6 General electrical characteristics

Test conditions (unless otherwise specified in the table): $V_{DD} = 1.8V$, $T_A = 25$ °C, 55% R.H.

Parameter		Symbol		Values		Unit	Note / Test Condition	
			Min.	Тур.	Max.			
Current	Clock Off Mode	I _{clock_off}		1	5	μΑ	CLOCK pulled low	
Consumption	Standby Mode	I _{standby}		95			No load on DATA	
	F _{clock} = 768kHz	I _{DD}		190	230		<5pF load on DATA	
	F _{clock} = 1.536MHz			450				
	F _{clock} = 2.4MHz			530				
	F _{clock} = 3.072MHz			580	680			
Short Circuit Cu	ırrent		1		20	mA	Grounded DATA pin	
Start up Time	After powered down, F _{clock} ≥ 768 kHz ⁵⁾				25	ms	Time after stable clock until sensitivity accuracy ±1.0dB	
	After powered down, F _{clock} < 768kHz ⁶⁾				45	ms	Time after stable clock until sensitivity accuracy ±1.0dB	
Power Supply Rejection		PSR _{1k_NM}		-88		dBFS	$100 \mathrm{mV}_{\mathrm{pp}}$ sine wave on V_{DD} swept from 200Hz to 20kHz.	
		PSR _{217_NM}		-90		dBFS(A)	100mV _{pp} , 217Hz square wave on V _{DD} . A-weighted	
Output Logic Lo	ow Level	V _{OL}			0.2xV _{DD}	V		
Output Logic Hi	igh Level	V _{OH}	0.8xV _{DD}					
Delay Time for I	DATA Driven	t _{DD}	60		100	ns	Delay time from CLOCK edge (0.5xV _{DD}) to DATA driven.	
Delay Time for DATA High-Z ⁷⁾		t _{HZ}	5		30	ns	Delay time from CLOCK edge (0.5xV _{DD}) to DATA high impedance state	
Delay Time for DATA Valid ⁸⁾		t _{DV}			140	ns	Delay time from CLOCK edge (0.5xV _{DD}) to DATA valid (<0.3xV _{DD} or >0.7xV _{DD})	
Power-on beha	viour		d microph	one signa	al is availabl		g V _{DD} and f _{clock} , remains ne consists of alternating	

Mode switch time to any specified frequency ≥ 768 kHz, from any specified frequency ≥ 768 kHz or Off. VDD is always present during mode switching.

Mode switch time to any specified frequency <768kHz, from any specified frequency or Off. VDD is always present during the mode switching

 $^{^{7}}$ t_{hold} is dependent on C_{load}

Load on data: C_{load}=100pF, R_{load}=100kΩ

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5 Electrical characteristics and parameters

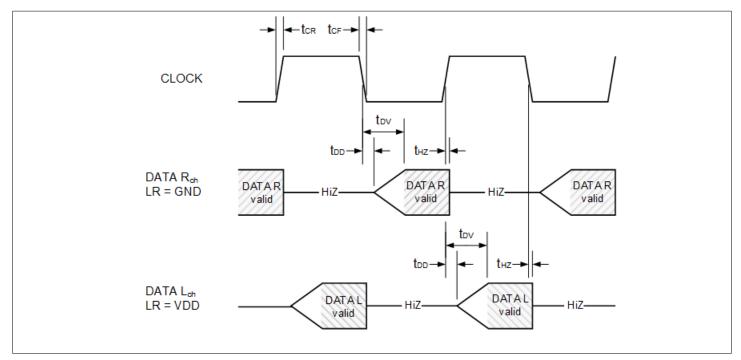


Figure 11 Timing diagram

5.4 Audio DC offset

The DC output level encoded in the DC bit stream is determined by the LR state on startup. In each case the DC output level is stable over time and does not vary with input signal level.

Table 7 DC output level using LR pin

LR state	DC output level (typical)	Unit
LR = GND	-90	dBFS
LR = VDD	-30	dBFS

1.1

5 Electrical characteristics and parameters



5.5 Stereo PDM configuration

The IM66D132HV01 is designed to function in circuits with one or two microphones on the PDM bus. When two microphones are connected, data is transmitted alternately according to the LR pin status of each microphone. When two microphones are connected to a shared PDM bus, the power modes of both microphones will be the same as both are controlled by the same PDM clock. The performance is unchanged relative to a single microphone per bus configuration.

Table 8 PDM channel configuration using LR pin.

Channel	Data driven	Data high-Z	LR connection
DATA1	Falling clock edge	Rising clock edge	GND
DATA2	Rising clock edge	Falling clock edge	V_{DD}

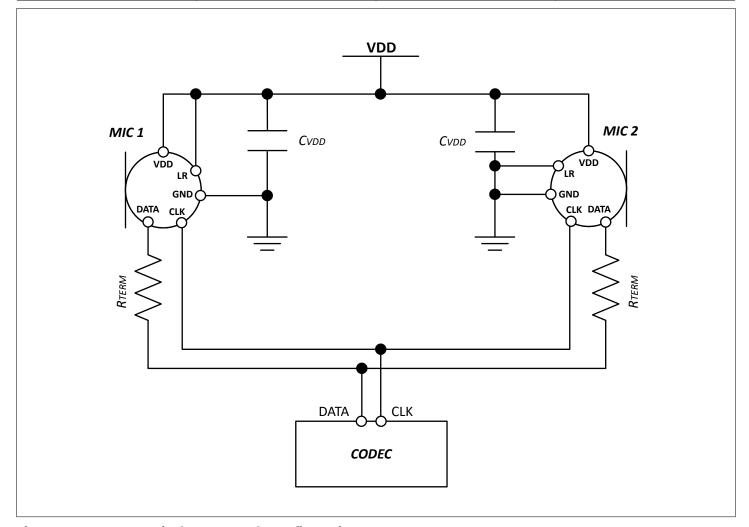


Figure 12 Typical stereo mode configuration

Note:

For best performance it is strongly recommended to place a $1\mu F$ ($C_{VDD_typical}$) capacitor between V_{DD} and ground. The capacitor should be placed as close to V_{DD} as possible. A termination resistor (R_{TERM}) of about 100Ω may be added to reduce the ringing and overshoot on the output signal.

6 Package information



6 Package information

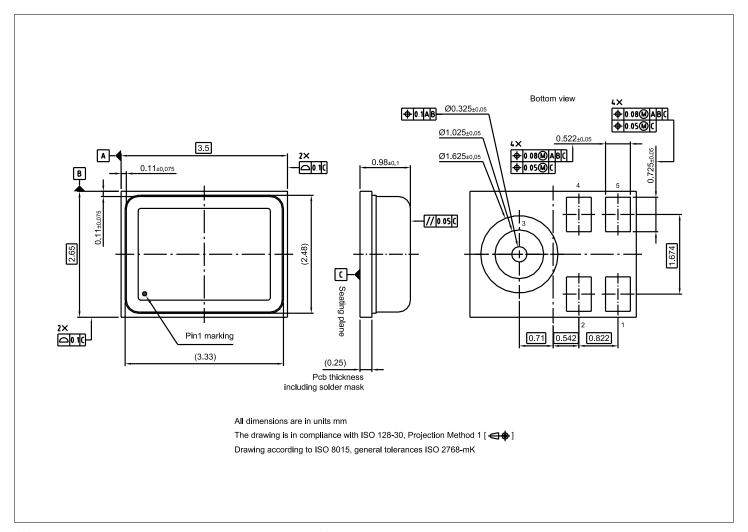


Figure 13 IM66D132HV01 package drawing

Table 9 IM66D132HV01 pin configuration

Pin Number	Name	Description
1	DATA	PDM data output
2	LR select	PDM left/right select
3	GND	Ground
4	CLOCK	PDM clock input
5	V _{DD}	Power supply

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7 Packing information



7 Packing information

For shipping and assembly the Infineon microphones are packed in product specific tape-and-reel carriers. A detailed drawing of the carrier can be seen in

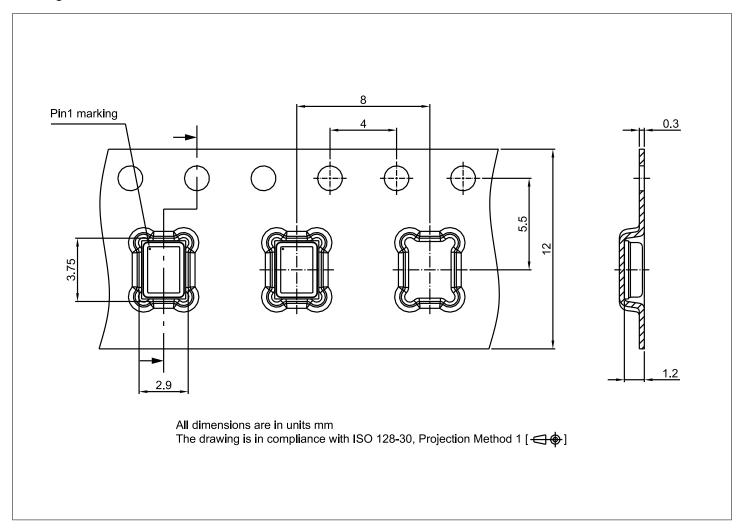


Figure 14 IM66D132HV01 tape and reel packing information

Table 10 IM66D132HV01 packaging information

Product	Type code	Reel diameter	Quantity per reel
IM66D132HV01	I66D31	13"	5000

1.1

8 Footprint and stencil recommendation



8 Footprint and stencil recommendation

The acoustic port hole diameter in the PCB should be larger than the acoustic port hole diameter of the MEMS microphone to ensure optimal performance. A PCB sound port size of diameter 0.6 mm is recommended.

The board pad and stencil aperture recommendations shown below are based on Non-Solder Mask Defined (NSMD) pads. The specific design rules of the board manufacturer should be considered for individual design optimizations or adaptations.

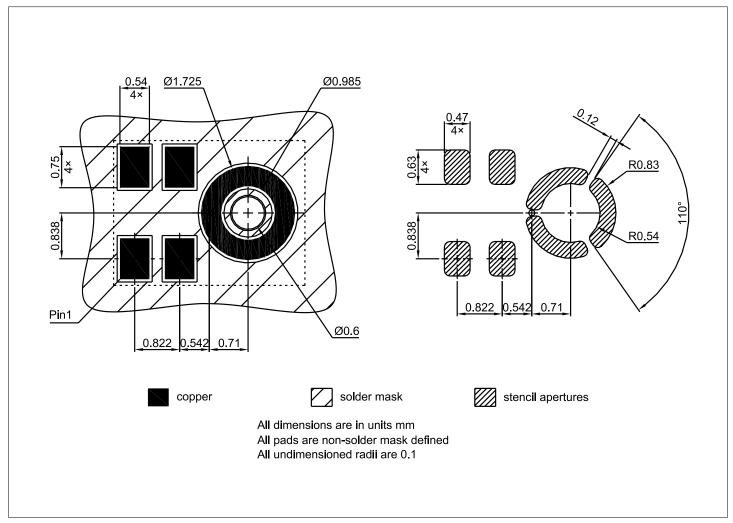


Figure 15 Footprint and stencil recommendation

9 Reflow soldering and board assembly



9 Reflow soldering and board assembly

Infineon MEMS microphones are qualified in accordance with the IPC/JEDEC J-STD-020D-01. The moisture sensitivity level of MEMS microphones is rated as MSL1. For PCB assembly of the MEMS microphone the widely used reflow soldering using a forced convection oven is recommended.

The soldering profile should be in accordance with the recommendations of the solder paste manufacturer to reach an optimal solder joint quality. The reflow profile shown in Figure 16 is recommended for board manufacturing with Infineon MEMS microphones.

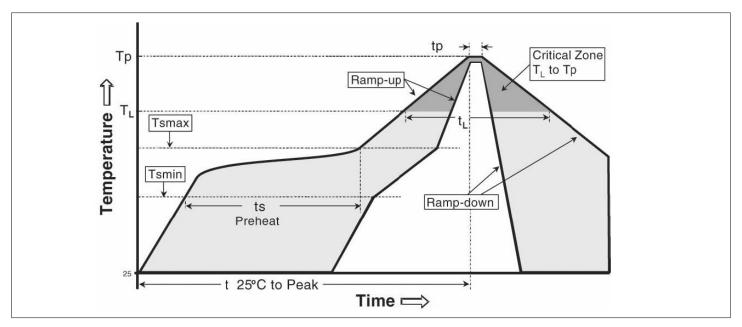


Figure 16 Recommended reflow profile

Reflow profile limits Table 11

Profile feature	Pb-Free assembly	Sn-Pb Eutectic assembly
Temperature Min (T _{smin})	150 °C	100 °C
Temperature Max (T _{smax})	200 °C	150 °C
Time (T _{smin} to T _{smax}) (t _s)	60-120 seconds	60-120 seconds
Ramp-up rate (T _L to T _P)	3 °C/second max.	3 °C/second max.
Liquidous temperature (T _L)	217 °C	183 °C
Time (t _L) maintained above T _L	60-150 seconds	60-150 seconds
Peak Temperature (T _p)	260°C +0°C/-5°C	235°C +0°C/-5°C
Time within 5°C of actual peak temperature (tp) ⁹⁾	20-40 seconds	10-30 seconds
Ramp-down rate	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	8 minutes max.	6 minutes max.

For further information please consult the 'General recommendation for assembly of Infineon packages' Note: document which is available on the Infineon Technologies web page

1.1

Tolerance for peak profile temperature (T_p) is defined as a supplier minimum and a user maximum

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9 Reflow soldering and board assembly

The MEMS microphones can be handled using industry standard pick and place equipment. Care should be taken to avoid damage to the microphone structure as follows:

- Do not pick the microphone with vacuum tools which make contact with the microphone acoustic port hole.
- The microphone acoustic port hole should not be exposed to vacuum, this can destroy or damage the MEMS.
- Do not blow air into the microphone acoustic port hole. If an air blow cleaning process is used, the port hole must be sealed to prevent particle contamination.
- It is recommended to perform the PCB assembly in a clean room environment in order to avoid microphone contamination.
- Air blow and ultrasonic cleaning procedures shall not be applied to MEMS Microphones. A no-clean paste is
 recommended for the assembly to avoid subsequent cleaning steps. The microphone MEMS can be severely
 damaged by cleaning substances.
- To prevent the blocking or partial blocking of the sound port during PCB assembly, it is recommended to cover the sound port with protective tape during PCB sawing or system assembly.
- Do not use excessive force to place the microphone on the PCB. The use of industry standard pick and place tools is recommended in order to limit the mechanical force exerted on the package.

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10 Reliability specifications



10 Reliability specifications

The microphone sensitivity after stress must deviate by no more than 3dB from the initial value.

Table 12 Reliability specification

Test	Abbreviation	Test Condition	Standard
High Temperature Operating Life	HTOL	T _a =+125°C, VDD=3.6V, 1000 hours	JESD22-A108
Low Temperature Operating Life	LTOL	T _a =-40°C, VDD=3.6V, 1000 hours	JESD22-A108
High Temperature Storage Life	HTSL	T _a =+125°C, 1000 hours	JESD22-A103
Low Temperature Storage Life	LTSL	T _a =-40°C, 1000 hours	JESD22-A119
Temperature Cycling	PC + TC	Pre conditioning MSL-1	JESD22-A113
		1000 cycles, -40°C to +125°C, 30 minutes per cycle	JESD22-A104
Temperature Humidity Bias	PC + THB	Pre conditioning MSL-1	JESD22-A113
		T _a =+85°C, R.H = 85%, VDD=3.6V, 1000 hours	JESD22-A101
Vibration Test	VVF	20Hz to 2000Hz with a peak acceleration of 20g in X, Y, and Z for 4 minutes each, total 4 -cycles	IEC 60068-2-6
Mechanical Shock	MS	10000g/0.2msec direction ±x,y,z, 5 shocks in each direction, 5 shocks in total	IEC 60068-2-27
Reflow Solder ¹⁰⁾	RS	3 reflow cycles, peak temperature = +260°C	IPC-JEDEC J-STD-020D-01
Electrostatic Discharge -System	ESD - SLT	3 air discharges of ±15kV via the lid	\dashv
Level Test		3 discharges of ±8kV direct contact to lid while V _{dd} is supplied according to the operational modes; (V _{dd} ground is separated from earth ground)	
Electrostatic Discharge - Human Body Model	ESD - HBM	1 pulse of ±2kV between all I/O pin combinations	JEDEC-JS001
Electrostatic Discharge - Charged Device Model	ESD - CDM	3 discharges of ±500V direct contact to I/O pins.	JEDEC JS-002
Latch Up	LU	Trigger current from ±100mA	JESD78E

The microphone sensitivity must deviate by no more than 1dB from the initial value after 3 reflow cycles.

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10 Reliability specifications



10.1 **Environmental robustness**

Infineon's latest Single Backplate MEMS technology delivers high ingress protection (IP57) on microphone level. The MEMS is designed to reduce the risk of mechanical blockage or electrical fail caused by water or dust.

Table 13 **Environmental robustness**

Test Standard	Test Condition
IP5x dust resistance ¹¹⁾	Arizona dust A4 coarse, vertical orientation, sound hole upwards, 10 cycles (15 minutes sedimentation, 6 sec blowing)
IPx7 water immersion ¹²⁾	Temporary immersion of 1 meters for 30 minutes. Microphone tested 6 hours after removal

The number "5" stands for the dust ingress rating or the capacity to withstand the effects of fine, abrasive dust particles.

¹² The "7" specifies the higher water immersion rating.

Datasheet

Revision history



Revision history

Document version	Date of release	Description of changes	
V1.0	2025-05-20	Initial release	
V1.1	2025-08-01	Additional information provided on storage temperature Added topic regarding free-field frequency response.	

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